

Features

- Split Gate Trench MOSFET Technology
- High Density Cell Design For Ultra Low $R_{DS(on)}$
- Moisture Sensitivity Level 3
- Halogen Free."Green"Device(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

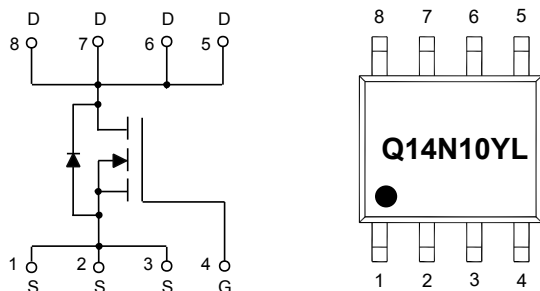
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient (Note 2)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	11	A
		7	
Pulsed Drain Current (Note 3)	I_{DM}	44	A
Total Power Dissipation (Note 4)	P_D	2.5	W
Single Pulsed Avalanche Energy (Note 5)	E_{AS}	121	mJ

Note:

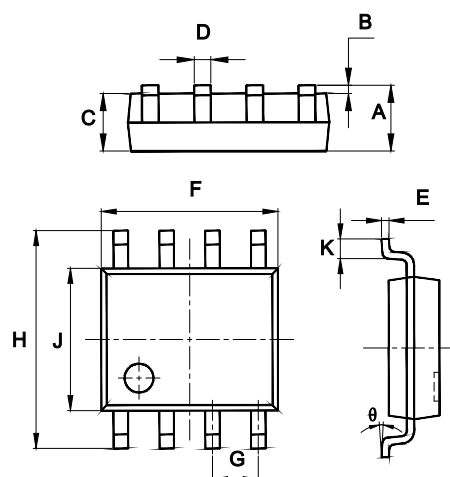
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.
5. $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\Omega$, $L = 2\text{mH}$.

Internal Structure and Marking Code



N-CHANNEL MOSFET

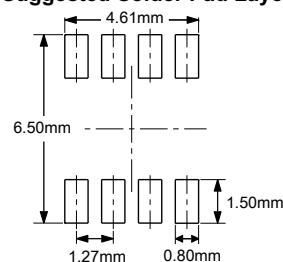
SOP-8



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.053	0.069	1.35	1.75	
B	0.004	0.010	0.10	0.25	
C	0.053	0.061	1.35	1.55	
D	0.013	0.020	0.33	0.51	
E	0.007	0.010	0.17	0.25	
F	0.185	0.200	4.70	5.10	
G	0.050		1.270		TYP.
H	0.228	0.244	5.80	6.20	
J	0.150	0.157	3.80	4.00	
K	0.016	0.050	0.40	1.27	
θ	0°	8°	0°	8°	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100			V
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.7	3	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =11A		11	14	mΩ
		V _{GS} =4.5V, I _D =11A		13	17	
Gate Resistance	R _g	f=1 MHz, Open drain		1.4		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				11	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =11A			1.2	V
Reverse Recovery Time	t _{rr}	I _F =11A, dI _F /dt=100A/μs		43		ns
Reverse Recovery Charge	Q _{rr}			33		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz		1800		pF
Output Capacitance	C _{oss}			590		
Reverse Transfer Capacitance	C _{rss}			20		
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =11A		30		nC
Gate-Source Charge	Q _{gs}			7.5		
Gate-Drain Charge	Q _{gd}			4.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} =50V, V _{GS} =10V, I _D =11A, R _G =3Ω		10		ns
Turn-On Rise Time	t _r			33		
Turn-Off Delay Time	t _{d(off)}			28		
Turn-Off Fall Time	t _f			9		

Curve Characteristics

Fig.1 - Typical Output Characteristics

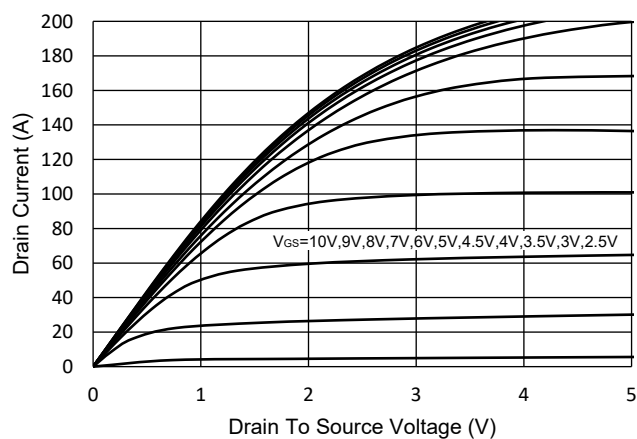


Fig.2 - Transfer Characteristics

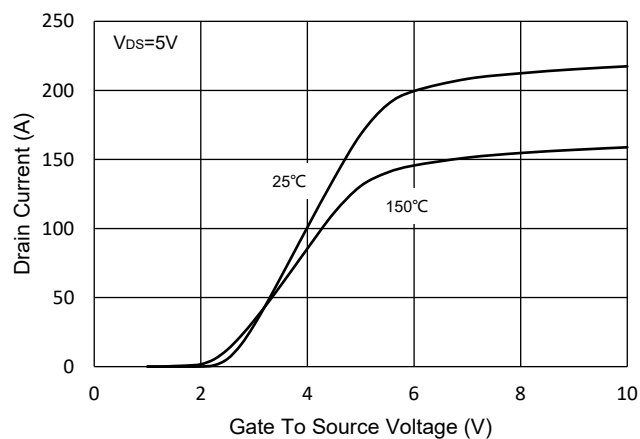


Fig.3 - $R_{DS(ON)}$ - V_{GS}

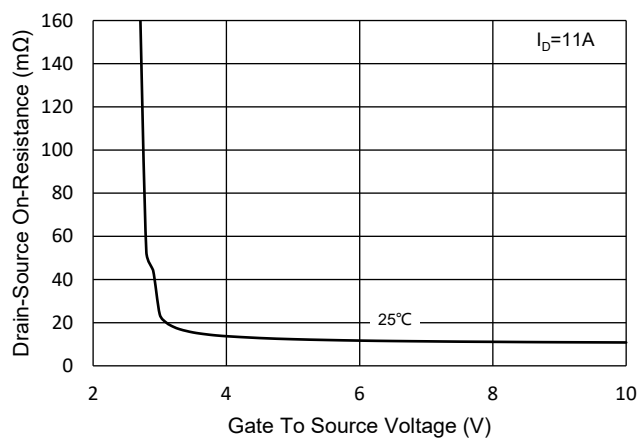


Fig.4 - $R_{DS(ON)}$ - I_D

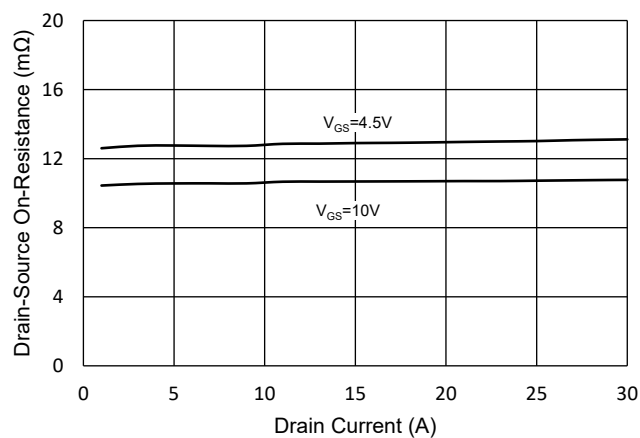


Fig. 5 - Capacitance Characteristics

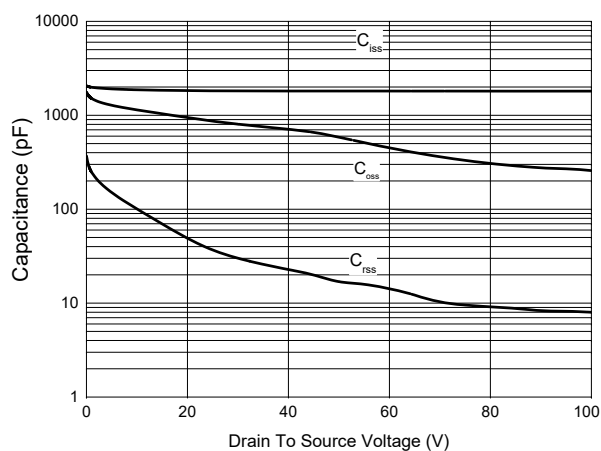
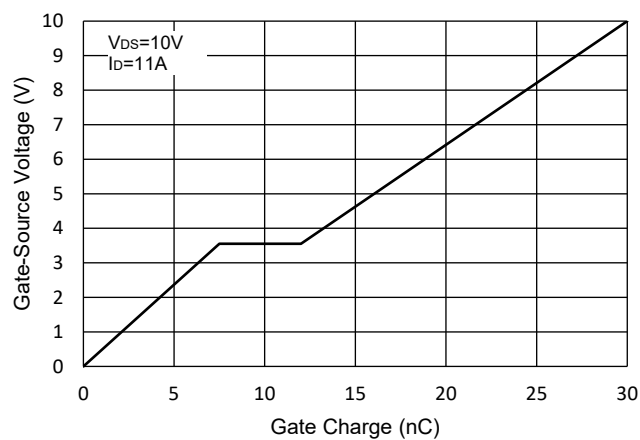


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

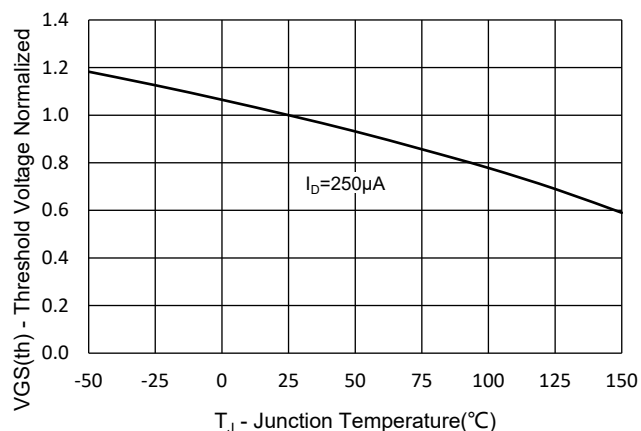


Fig.8 - Normalized On Resistance Characteristics

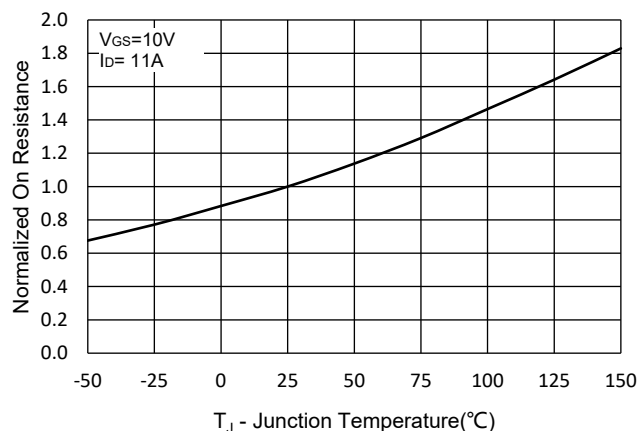


Fig.9 - $I_S - V_{SD}$

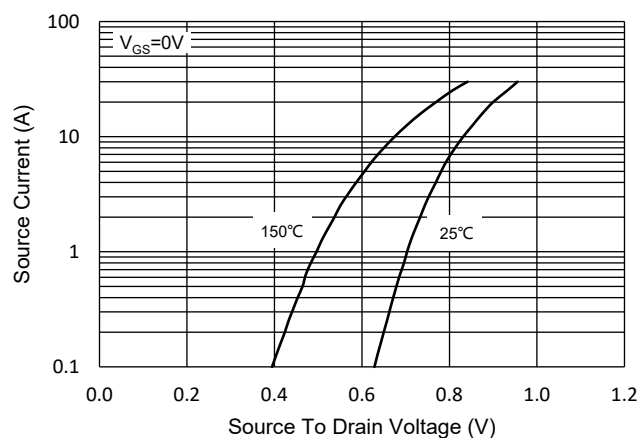


Fig.10 - Drain Current

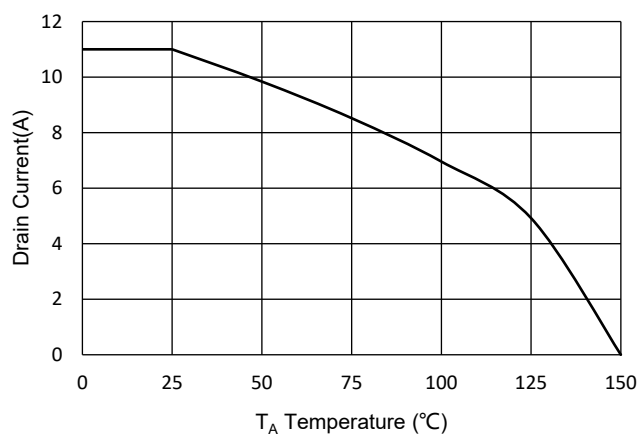
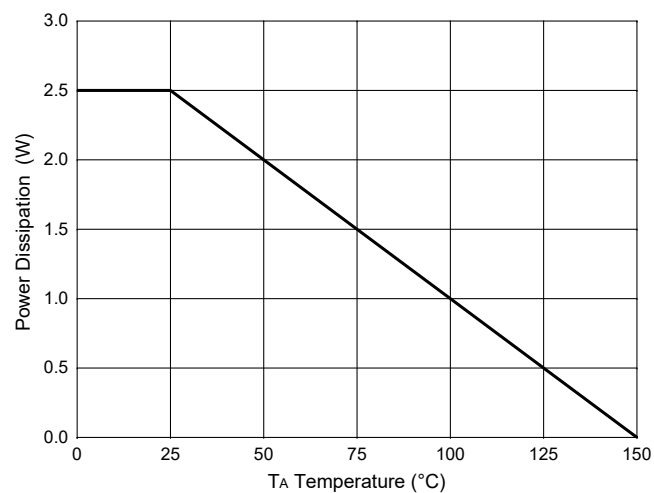


Fig.11-PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

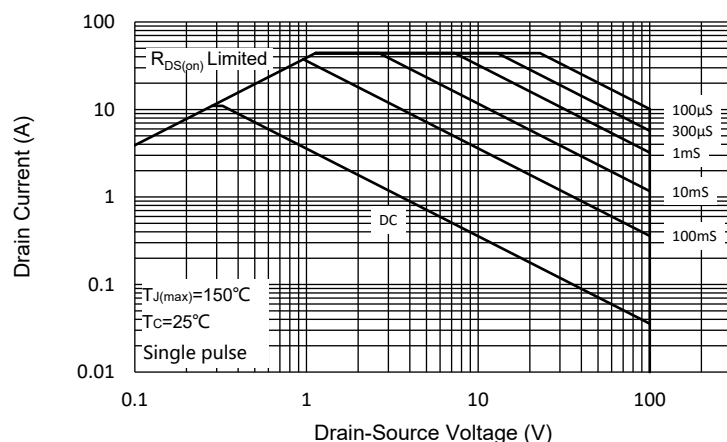
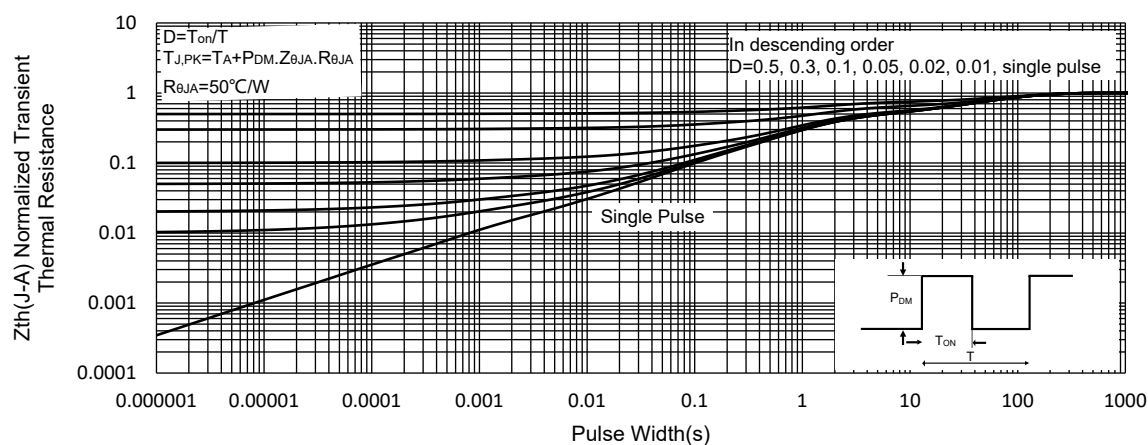


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

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